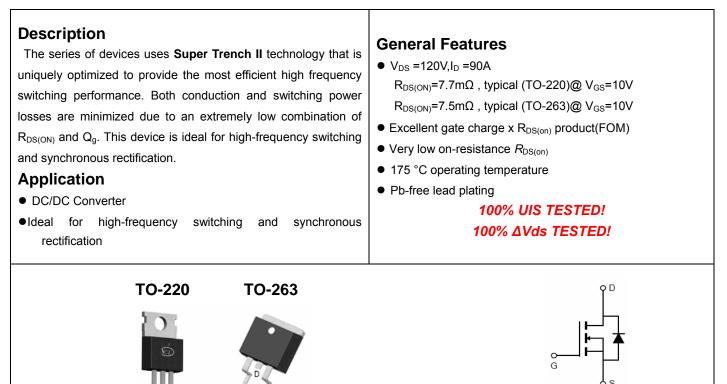


NCE N-Channel Super Trench II Power MOSFET



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP080N12	NCEP080N12	TO-220	-	-	-
NCEP080N12D	NCEP080N12D	TO-263	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	120	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	90	А
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	64	A
Pulsed Drain Current ^(Note 1)	I _{DM}	360	A
Maximum Power Dissipation	PD	140	W
Derating factor		0.93	W/°C
Single pulse avalanche energy (Note 4)	E _{AS}	352	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{ extsf{ heta}JC}$	1.07	°C /W]
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Electrical Characteristics (T_c=25[°]C unless otherwise noted) Symbol Condition Min Parameter Typ Max Unit **Off Characteristics** Drain-Source Breakdown Voltage V_{GS}=0V I_D=250µA V **BV**_{DSS} 120 _ Zero Gate Voltage Drain Current V_{DS}=120V, V_{GS}=0V IDSS -1 μA Gate-Body Leakage Current IGSS V_{GS}=±20V,V_{DS}=0V ±100 nA _ _ On Characteristics (Note 3) Gate Threshold Voltage V_{DS}=V_{GS}, I_D=250µA 2.0 3.0 4.0 V V_{GS(th)} TO-220 7.7 8.0 Drain-Source On-State Resistance V_{GS}=10V, I_D=45A R_{DS(ON)} mΩ TO-263 7.5 8.0 V_{DS}=5V,I_D=45A Forward Transconductance 55 _ S **g**_{FS} Dynamic Characteristics (Note3) Input Capacitance Clss 3715 pF _ _ V_{DS}=60V, V_{GS}=0V, **Output Capacitance** C_{oss} 275 pF _ _ F=1.0MHz **Reverse Transfer Capacitance** C_{rss} 18 рF _ _ Switching Characteristics (Note 3) Turn-on Delay Time 20 nS t_{d(on)} _ Turn-on Rise Time tr 16 nS _ _ V_{DD} =60V,I_D=45A V_{GS}=10V,R_G=1.6Ω Turn-Off Delay Time 45 t_{d(off)} -_ nS Turn-Off Fall Time tf -12 nS **Total Gate Charge** 58 nC Qq -_ V_{DS}=60V,I_D=45A, Gate-Source Charge Q_{qs} 21 nC --V_{GS}=10V Gate-Drain Charge Q_{gd} 14.5 nC **Drain-Source Diode Characteristics** Diode Forward Voltage (Note 2) V_{SD} V_{GS}=0V,I_S=45A 1.2 V _ **Diode Forward Current** 90 А $I_{\rm S}$ _ _ **Reverse Recovery Time** $T_J = 25^{\circ}C, I_F = 90A$ nS t_{rr} -65 di/dt = 100A/µs^(Note3) **Reverse Recovery Charge** Qrr -105 nC _

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

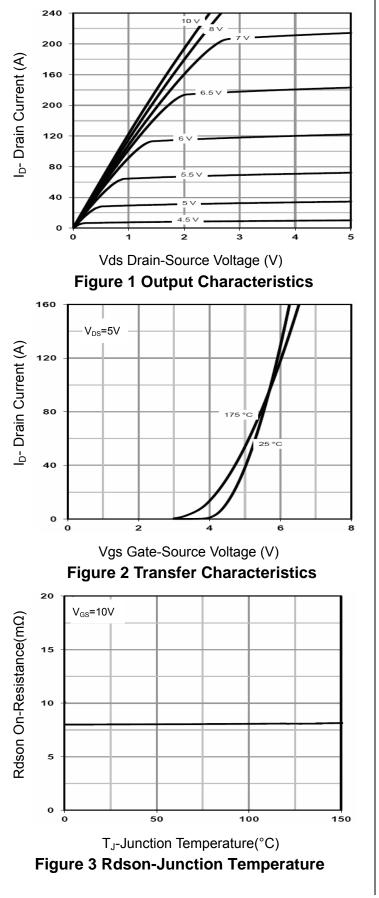
2. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

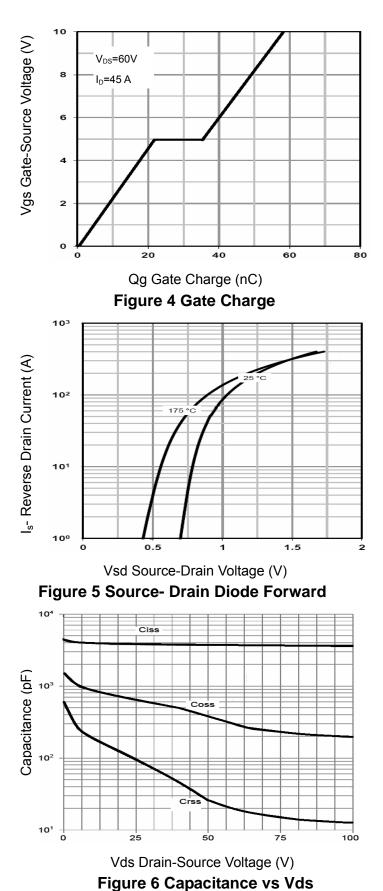
3. Guaranteed by design, not subject to production

4. EAS condition : Tj=25 $^\circ C$,V_DD=50V,V_G=10V,L=0.25mH,Rg=25 Ω



Typical Electrical and Thermal Characteristics







NCEP080N12,NCEP080N12D

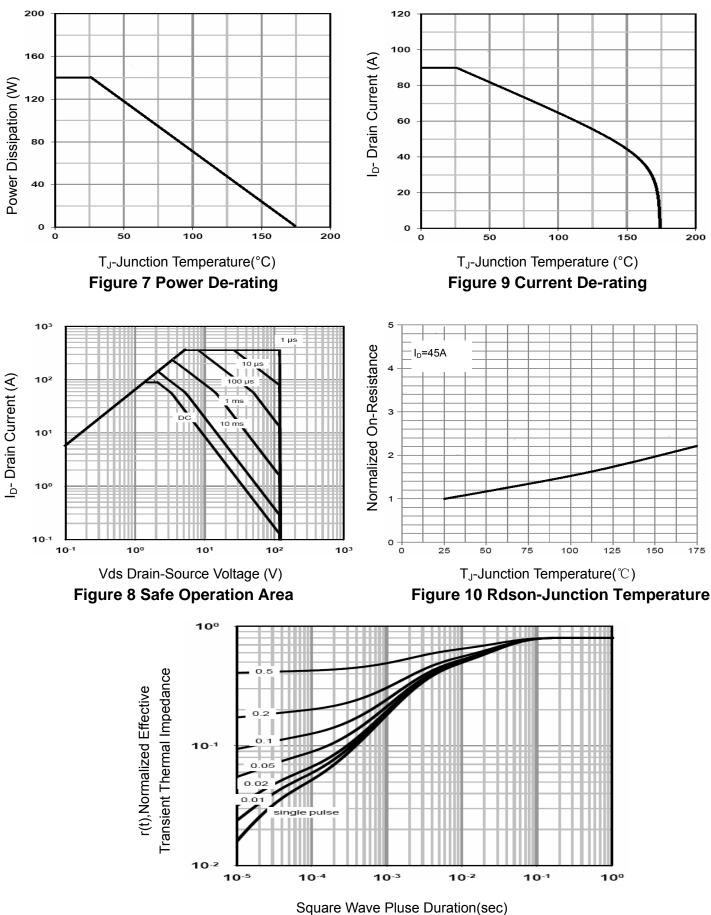
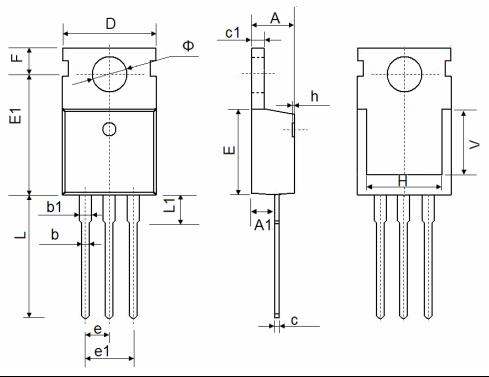


Figure 11 Normalized Maximum Transient Thermal Impedance



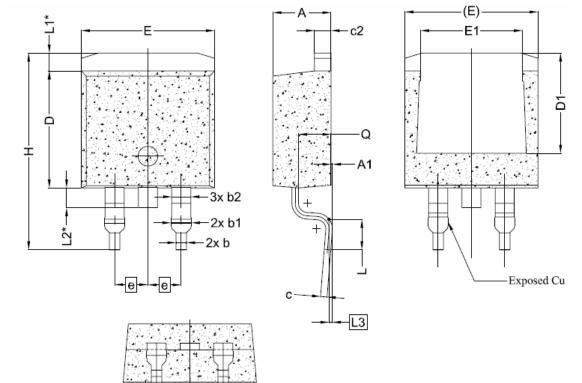
TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
С	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
е	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
Н	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276	REF.
Ф	3.400	3.800	0.134	0.150



TO-263-2L Package Information



Querrale al	Dimensions In Millimeters			
Symbol	Min.	Nom.	Max.	
A	4.24	4.44	4.64	
A1	0.00	0.10	0.25	
b	0.70	0.80	0.90	
b1	1.20	1.55	1.75	
b2	1.20	1.45	1.70	
с	0.40	0.50	0.60	
c2	1.15	1.27	1.40	
D	8.82	8.92	9.02	
D1	6.86	7.65	-	
E	9.96	10.16	10.36	
E1	6.89	7.77	7.89	
е	2.54BSC			
Н	14.61	15.00	15.88	
L	1.78	2.32	2.79	
L1	1.36 REF.			
L2	1.50 REF.			
L3	0.25 BSC			
Q	2.30	2.48	2.70	



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